

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	1.1 Ω @10V	0.6A
	1.3 Ω @4.5V	

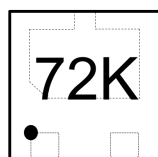
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(on)}$
- Low Gate Charge
- ESD Protect

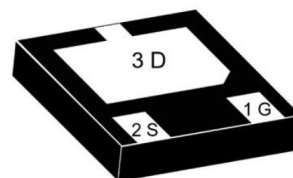
Application

- Load Switch
- DC/DC Converter

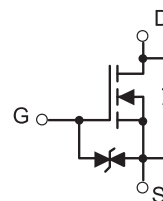
MARKING:



DFN1.1X1.1-3L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	60	V
Gate - Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ^{1,5}	$T_A = 25^\circ\text{C}$	I_D	0.6	A
	$T_A = 100^\circ\text{C}$	I_D	0.39	A
Pulsed Drain Current ²		I_{DM}	2.4	A
Power Dissipation ^{4,5}	$T_A = 25^\circ\text{C}$	P_D	420	mW
Thermal Resistance from Junction to Ambient ⁵		$R_{\theta JA}$	300	$^\circ\text{C}/\text{W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

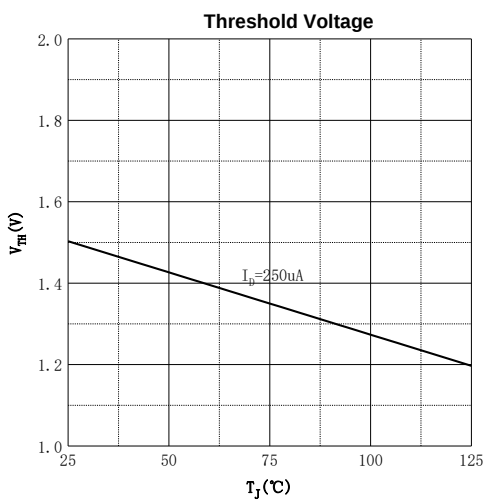
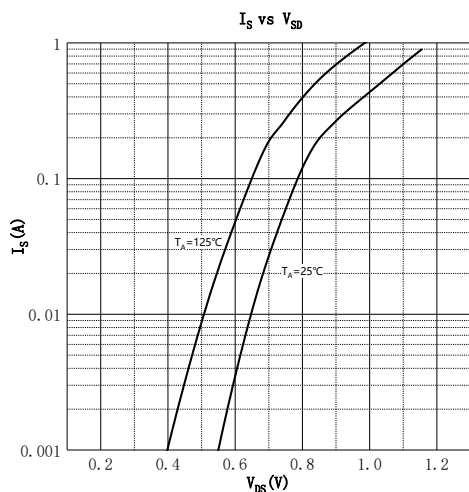
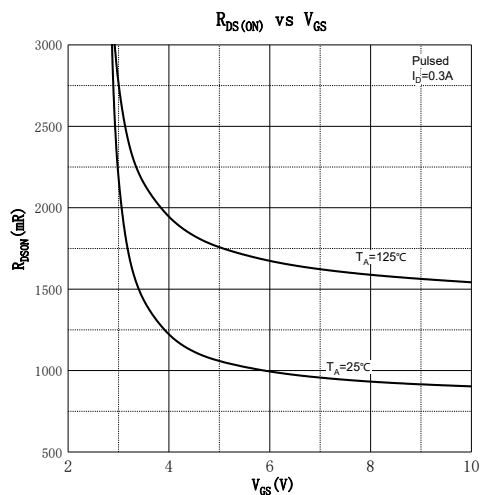
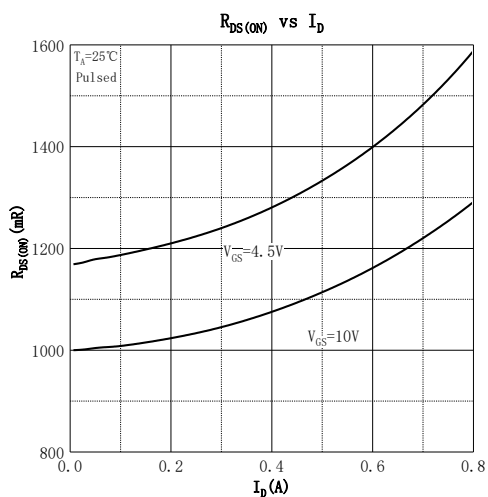
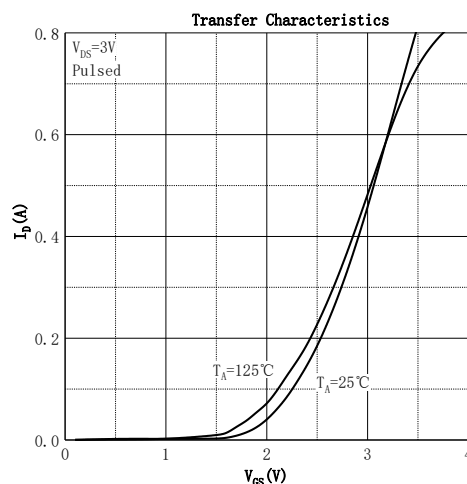
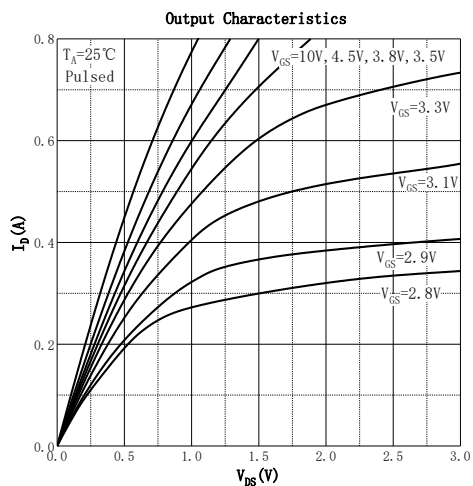
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

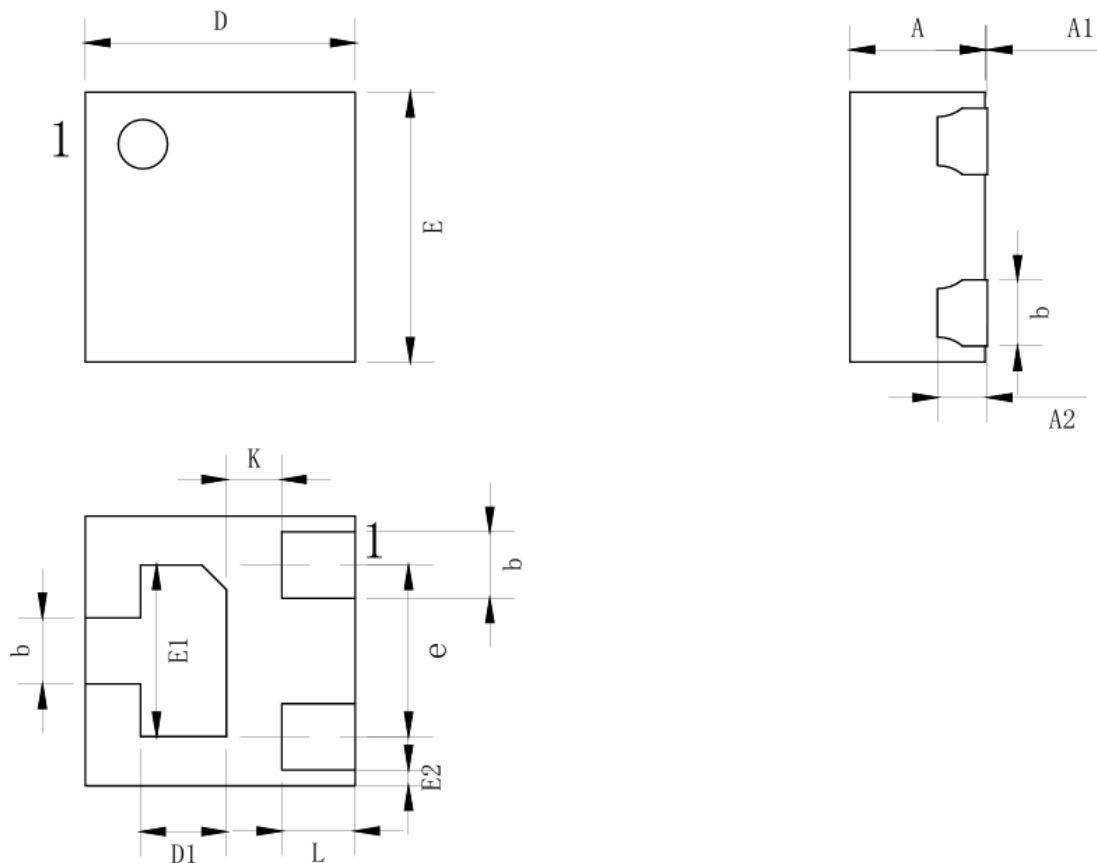
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V , I _D = 250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±5	μA
On Characteristics ³						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.5	2.0	V
Drain-source On-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 0.3A		1.1	1.5	Ω
		V _{GS} = 4.5V, I _D = 0.2A		1.3	2.5	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		26		pF
Output Capacitance	C _{oss}			6		
Reverse Transfer Capacitance	C _{rss}			3		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		120		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 15V, V _{GS} = 10V, I _D =20A		2.2		nC
Gate-source Charge	Q _{gs}			0.5		
Gate-drain Charge	Q _{gd}			0.9		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30V, V _{GS} = 10V, R _L = 100Ω, R _G = 3Ω		3		ns
Turn-on Rise Time	t _r			3		
Turn-off Delay Time	t _{d(off)}			12		
Turn-off Fall Time	t _f			10		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V _{SD}	V _{GS} = 0V, I _S = 0.3A			1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



DFN1.1X1.1-3L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.017	0.022
A1	0.000	0.050	0.000	0.002
A2	0.203TYP		0.008TYP	
b	0.220	0.320	0.008	0.013
D	1.050	1.150	0.041	0.046
D1	0.300	0.400	0.011	0.016
E	1.050	1.150	0.041	0.046
E1	0.650	0.750	0.025	0.030
E2	0.065TYP		0.026 TYP	
E	0.700 BSC		0.028 BSC	
K	0.220 BSC		0.009 BSC	
L	0.250	0.350	0.010	0.014

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.